## **Freescale Semiconductor**

Data Sheet: Technical Data

## Document Number: MCF51AC256 Rev.7, 9/2011

# MCF51AC256 Series ColdFire Microcontroller

## Covers: MCF51AC256A MCF51AC256B MCF51AC128A MCF51AC128C

The MCF51AC256 series are members of the ColdFire<sup>®</sup> family of 32-bit variable-length reduced instruction set (RISC) microcontroller. This document provides an overview of the MCF51AC256 series, focusing on its highly integrated and diverse feature set.

The MCF51AC256 series are based on the V1 ColdFire core and operates at processor core speeds up to 50.33 MHz. As part of Freescale's Controller Continuum<sup>®</sup>, it is an ideal upgrade for designs based on the MC9S08AC128 series of 8-bit microcontrollers.

The MCF51AC256 features the following functional units:

- V1 ColdFire core with background debug module
- Up to 256 KB of flash memory
- Up to 32 KB of static RAM (SRAM)
- Up to two analog comparators (ACMP)
- Analog-to-digital converter (ADC) with up to 24 channels
- Controller-area network (CAN)
- Cyclic redundancy check (CRC)
- Inter-integrated circuit (IIC)
- Keyboard interrupt (KBI)
- Multipurpose clock generator (MCG)
- Rapid general-purpose input/output (RGPIO)

# 80 LQFP 64 LQFP 14 mm × 14 mm 64 QFP 10 mm × 10 mm 64 QFP 10 mm × 10 mm 64 QFP 10 mm × 10 mm 14 mm × 14 mm

- Two serial communications interfaces (SCI)
- Up to two serial peripheral interfaces (SPI)
- Two flexible timer modules (FTM)
- Timer pulse-width modulator (TPM)

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# 1.1 Device Comparison

The MCF51AC256 series is summarized in Table 1.

## Table 1. MCF51AC256 Series Device Comparison

Facture	MCF51	AC256A	MCF51AC256B		MCF51AC128A		MCF51AC128C		28C	
Feature -		64-pin	80-pin	64-pin	44-pin	80-pin	64-pin	80-pin	64-pin	44-pin
Flash memory size (Kbytes)			256				I	128		
RAM size (Kbytes)			32					32 or 16 <sup>1</sup>		
V1 ColdFire core with BDM (background debug module)					١	⁄es				
ACMP1 (analog comparator)					١	⁄es				
ACMP2 (analog comparator)	Ye	es	Ye	es	No		Y	es		No
ADC (analog-to-digital converter) channels (12-bit)	24	20	24	20	9	24	20	24	20	9
CAN (controller area network)	Ye	es		No		Ye	es		No	
COP (computer operating properly)					١	⁄es				
CRC (cyclic redundancy check)	Yes									
RTI	Yes									
DBG (debug)	Yes									
IIC1 (inter-integrated circuit)	Yes									
IRQ (interrupt request input)					١	⁄es				
INTC (interrupt controller)					١	⁄es				
KBI (keyboard interrupts)					١	⁄es				
LVD (low-voltage detector)					١	⁄es				
MCG (multipurpose clock generator)					١	⁄es				
OSC (crystal oscillator)					١	⁄es				
Port I/O <sup>2</sup>	69	54	69	54	36	69	54	69	54	36
RGPIO (rapid general-purpose I/O)		1	6	•	12		1	6		12
SCI1, SCI2 (serial communications interfaces)	Yes									
SPI1 (serial peripheral interface)					١	⁄es				
SPI2 (serial peripheral interface)	Yes	No	Yes	N	lo	Yes	No	Yes	N	0
FTM1 (flexible timer module) channels			6		4		. (	6		4
FTM2 channels	6	2	6	2	2	6	2	6	2	2

Feature	MCF51AC256A		MCF51AC256B		MCF51AC128A		MCF51AC128C			
i cature	80-pin	64-pin	80-pin	64-pin	44-pin	80-pin	64-pin	80-pin	64-pin	44-pin
TPM3 (timer pulse-width modulator) channels					2				<u>.</u>	
VBUS (debug visibility bus)	Yes	No	Yes	N	lo	Yes	No	Yes	N	0

Table 1. MCF51AC256 Series Device Comparison (continued)

<sup>1</sup> The members of MCF51AC128A with CAN support have 32 KB RAM. The other members have 16 KB RAM.

 $^2~$  Up to 16 pins on Ports E and F are shared with the ColdFire Rapid GPIO module.

## 1.2 Block Diagram

Figure 1 shows the connections between the MCF51AC256 series pins and modules.



Figure 1. MCF51AC256 Series Block Diagram

## 1.3 Features

# Table 2 describes the functional units of the MCF51AC256 series.Table 2. MCF51AC256 Series Functional Units

Functional Unit	Function
CF1 Core (V1 ColdFire core)	Executes programs and interrupt handlers
BDM (background debug module)	Provides single pin debugging interface (part of the V1 ColdFire core)
DBG (debug)	Provides debugging and emulation capabilities (part of the V1 ColdFire core)
VBUS (debug visibility bus)	Allows for real-time program traces (part of the V1 ColdFire core)
SIM (system integration module)	Controls resets and chip level interfaces between modules
Flash (flash memory)	Provides storage for program code, constants and variables
RAM (random-access memory)	Provides storage for program variables
RGPIO (rapid general-purpose input/output)	Allows for I/O port access at CPU clock speeds
VREG (voltage regulator)	Controls power management across the device
COP (computer operating properly)	Monitors a countdown timer and generates a reset if the timer is not regularly reset by the software
LVD (low-voltage detect)	Monitors internal and external supply voltage levels, and generates a reset or interrupt when the voltages are too low
CF1_INTC (interrupt controller)	Controls and prioritizes all device interrupts
ADC (analog-to-digital converter)	Measures analog voltages at up to 12 bits of resolution
FTM1, FTM2 (flexible timer/pulse-width modulators)	Provides a variety of timing-based features
TPM3 (timer/pulse-width modulator)	Provides a variety of timing-based features
CRC (cyclic redundancy check)	Accelerates computation of CRC values for ranges of memory
ACMP1, ACMP2 (analog comparators)	Compares two analog inputs
IIC (inter-integrated circuit)	Supports standard IIC communications protocol
KBI (keyboard interrupt)	Provides pin interrupt capabilities
MCG (multipurpose clock generator)	Provides clocking options for the device, including a phase-locked loop (PLL) and frequency-locked loop (FLL) for multiplying slower reference clock sources
OSC (crystal oscillator)	Allows a crystal or ceramic resonator to be used as the system clock source or reference clock for the PLL or FLL
LPO (low-power oscillator)	Provides a second clock source for COP and RTI.
CAN (controller area network)	Supports standard CAN communications protocol
SCI1, SCI2 (serial communications interfaces)	Serial communications UARTs capable of supporting RS-232 and LIN protocols
SPI1 (8-bit serial peripheral interfaces)	Provides 8-bit 4-pin synchronous serial interface
SPI2 (16-bit serial peripheral interfaces)	Provides 16-bit 4-pin synchronous serial interface with FIFO

## 1.3.1 Feature List

- 32-bit Version 1 ColdFire® central processor unit (CPU)
  - Up to 50.33 MHz at 2.7 V 5.5 V
  - Provide 0.94 Dhrystone 2.1 DMIPS per MHz performance when running from internal RAM (0.76 DMIPS per MHz when running from flash)
  - Implements instruction set revision C (ISA\_C)
- On-chip memory
  - Up to 256 KB flash memory read/program/erase over full operating voltage and temperature
  - Up to 32 KB static random access memory (SRAM)
  - Security circuitry to prevent unauthorized access to SRAM and flash contents
- Power-Saving Modes
  - Three low-power stop plus wait modes
  - Peripheral clock enable register can disable clocks to unused modules, reducing currents; allows clocks to remain enabled to specific peripherals in stop3 mode
- System protection features
  - Watchdog computer operating properly (COP) reset with options to run from independent LPO clock or bus clock
  - Low-voltage detection with reset or interrupt
  - Illegal opcode and illegal address detection with programmable reset or exception response
  - Flash block protection
- Debug support
  - Single-wire background debug interface
  - Real-time debug support, with 6 hardware breakpoints (4 PC, 1 address pair and 1 data) that can be configured into a 1- or 2-level trigger
  - On-chip trace buffer provides programmable start/stop recording conditions plus support for continuous or PC-profiling modes
  - Support for real-time program (and optional partial data) trace using the debug visibility bus
- V1 ColdFire interrupt controller (CF1\_INTC)
  - Support of 40 peripheral I/O interrupt requests plus seven software (one per level) interrupt requests
  - Fixed association between interrupt request source and level plus priority, up to two requests can be remapped to the highest maskable level + priority
  - Unique vector number for each interrupt source
  - Support for service routine interrupt acknowledge (software IACK) read cycles for improved system performance
- Multipurpose clock generator (MCG)
  - Oscillator (XOSC); loop-control Pierce oscillator; crystal or ceramic resonator range of 31.25 kHz to 38.4 kHz or 1 MHz to 16 MHz
  - LPO clock as an optional independent clock source for COP and RTI
  - FLL/PLL controlled by internal or external reference

- Trimmable internal reference allows 0.2% resolution and 2% deviation
- Analog-to-digital converter (ADC)
  - 24 analog inputs with 12 bits resolution
  - Output formatted in 12-, 10- or 8-bit right-justified format
  - Single or continuous conversion (automatic return to idle after single conversion)
  - Operation in low-power modes for lower noise operation
  - Asynchronous clock source for lower noise operation
  - Automatic compare with interrupt for less-than, or greater-than or equal-to, programmable value
  - On-chip temperature sensor
- Flexible timer/pulse-width modulators (FTM)
  - 16-bit Free-running counter or a counter with initial and final value. The counting can be up and unsigned, up and signed, or up-down and unsigned
  - Up to 6 channels, and each channel can be configured for input capture, output compare or edge-aligned PWM mode, all channels can be configured for center-aligned PWM mode
    - Channels can operate as pairs with equal outputs, pairs with complimentary outputs or independent channels (with independent outputs)
    - Each pair of channels can be combined to generate a PWM signal (with independent control of both edges of PWM signal)
    - Deadtime insertion is available for each complementary pair
  - The load of the FTM registers which have write buffer can be synchronized; write protection for critical registers
  - Generation of the triggers to ADC (hardware trigger)
  - A fault input for global fault control
  - Backwards compatible with TPM
- Timer/pulse width modulator (TPM)
  - 16-bit free-running or modulo up/down count operation
  - Two channels, each channel may be input capture, output compare, or edge-aligned PWM
  - One interrupt per channel plus terminal count interrupt
- Cyclic redundancy check (CRC) generator
  - High speed hardware CRC generator circuit using 16-bit shift register
  - CRC16-CCITT compliancy with  $x^{16} + x^{12} + x^5 + 1$  polynomial
  - Error detection for all single, double, odd, and most multi-bit errors
  - Programmable initial seed value
- Analog comparators (ACMP)
  - Full rail to rail supply operation
  - Selectable interrupt on rising edge, falling edge, or either rising or falling edges of comparator output
  - Option to compare to fixed internal bandgap reference voltage
  - Option to allow comparator output to be visible on a pin, ACMPxO

- Inter-integrated circuit (IIC)
  - Compatible with IIC bus standard
  - Multi-master operation
  - Software programmable for one of 64 different serial clock frequencies
  - Interrupt driven byte-by-byte data transfer
  - Arbitration lost interrupt with automatic mode switching from master to slave
  - Calling address identification interrupt
  - Bus busy detection
  - 10-bit address extension
- Controller area network (CAN)
  - Implementation of the CAN protocol Version 2.0A/B
    - Standard and extended data frames
    - Zero to eight bytes data length
    - Programmable bit rate up to 1 Mbps
    - Support for remote frames
  - Five receive buffers with FIFO storage scheme
  - Three transmit buffers with internal prioritization using a "local priority" concept
  - Flexible maskable identifier filter supports two full-size (32-bit) extended identifier filters, four 16-bit filters, or eight 8-bit filters
  - Programmable wakeup functionality with integrated low-pass filter
  - Programmable loopback mode supports self-test operation
  - Programmable listen-only mode for monitoring of CAN bus
  - Programmable bus-off recovery functionality
  - Separate signalling and interrupt capabilities for all CAN receiver and transmitter error states (warning, error passive, bus-off)
  - Internal timer for time-stamping of received and transmitted messages
- Serial communications interfaces (SCI)
  - Full-duplex, standard non-return-to-zero (NRZ) format
  - Double-buffered transmitter and receiver with separate enables
  - Programmable baud rates (13-bit modulo divider)
  - Interrupt-driven or polled operation
  - Hardware parity generation and checking
  - Programmable 8-bit or 9-bit character length
  - Receiver wakeup by idle-line or address-mark
  - Optional 13-bit break character generation / 11-bit break character detection
  - Selectable transmitter output polarity
- Serial peripheral interfaces (SPI)
  - Master or slave mode operation
  - Full-duplex or single-wire bidirectional option
  - Programmable transmit bit rate

- Double-buffered transmit and receive
- Serial clock phase and polarity options
- Slave select output
- Selectable MSB-first or LSB-first shifting
- 16-bit and FIFO operations in SPI2
- Input/Output
  - 69 GPIOs
  - 8 keyboard interrupt pins with selectable polarity
  - Hysteresis and configurable pull-up device on all input pins; Configurable slew rate and drive strength on all output pins
  - 16-bits Rapid GPIO pins connected to the processor's local 32-bit platform bus with set, clear, and faster toggle functionality

## 1.4 Part Numbers



 Table 3. Orderable Part Number Summary

Freescale Part Number	Description	Flash / SRAM (Kbytes)	Package	Temperature
MCF51AC256AVFUE	MCF51AC256 ColdFire Microcontroller with CAN	256 / 32	64 QFP	–40°C to 105°C
MCF51AC256BVFUE	MCF51AC256 ColdFire Microcontroller without CAN	256 / 32	64 QFP	–40°C to 105°C
MCF51AC256AVLKE	MCF51AC256 ColdFire Microcontroller with CAN	256 / 32	80 LQFP	–40°C to 105°C
MCF51AC256BVLKE	MCF51AC256 ColdFire Microcontroller without CAN	256 / 32	80 LQFP	–40°C to 105°C
MCF51AC256AVPUE	MCF51AC256 ColdFire Microcontroller with CAN	256 / 32	64 LQFP	–40°C to 105°C
MCF51AC256BVPUE	MCF51AC256 ColdFire Microcontroller without CAN	256 / 32	64 LQFP	–40°C to 105°C
MCF51AC128AVFUE	MCF51AC128 ColdFire Microcontroller with CAN	128 / 32	64 QFP	–40°C to 105°C
MCF51AC128CVFUE	MCF51AC128 ColdFire Microcontroller without CAN	128 / 16	64 QFP	–40°C to 105°C
MCF51AC128AVLKE	MCF51AC128 ColdFire Microcontroller with CAN	128 / 32	80 LQFP	–40°C to 105°C
MCF51AC128CVLKE	MCF51AC128 ColdFire Microcontroller without CAN	128 / 16	80 LQFP	–40°C to 105°C
MCF51AC128AVPUE	MCF51AC128 ColdFire Microcontroller with CAN	128 / 32	64 LQFP	–40°C to 105°C
MCF51AC128CVPUE	MCF51AC128 ColdFire Microcontroller without CAN	128 / 16	64 LQFP	–40°C to 105°C
MCF51AC256ACFUE	MCF51AC256 ColdFire Microcontroller with CAN	256 / 32	64 QFP	–40°C to 85°C
MCF51AC256BCFUE	MCF51AC256 ColdFire Microcontroller without CAN	256 / 32	64 QFP	–40°C to 85°C
MCF51AC256ACLKE	MCF51AC256 ColdFire Microcontroller with CAN	256 / 32	80 LQFP	–40°C to 85°C
MCF51AC256BCLKE	MCF51AC256 ColdFire Microcontroller without CAN	256 / 32	80 LQFP	–40°C to 85°C

MCF51AC256ACPUE	MCF51AC256 ColdFire Microcontroller with CAN	256 / 32	64 LQFP	–40°C to 85°C
MCF51AC256BCPUE	MCF51AC256 ColdFire Microcontroller without CAN	256 / 32	64 LQFP	–40°C to 85°C
MCF51AC256BCFGE	MCF51AC256 ColdFire Microcontroller without CAN	256/32	44 LQFP	–40°C to 85°C
MCF51AC128ACFUE	MCF51AC128 ColdFire Microcontroller with CAN	128 / 32	64 QFP	–40°C to 85°C
MCF51AC128CCFUE	MCF51AC128 ColdFire Microcontroller without CAN	128 / 16	64 QFP	–40°C to 85°C
MCF51AC128ACLKE	MCF51AC128 ColdFire Microcontroller with CAN	128 / 32	80 LQFP	–40°C to 85°C
MCF51AC128CCLKE	MCF51AC128 ColdFire Microcontroller without CAN	128 / 16	80 LQFP	–40°C to 85°CC
MCF51AC128ACPUE	MCF51AC128 ColdFire Microcontroller with CAN	128 / 32	64 LQFP	–40°C to 85°C
MCF51AC128CCPUE	MCF51AC128 ColdFire Microcontroller without CAN	128 / 16	64 LQFP	–40°C to 85°C
MCF51AC128CCFGE	MCF51AC128 ColdFire Microcontroller without CAN	128 / 16	44 LQFP	–40°C to 85°C

## Table 3. Orderable Part Number Summary

## 1.5 Pinouts and Packaging

Figure 2 shows the pinout of the 80-pin LQFP.



Figure 2. MCF51AC256 Series ColdFire Microcontroller 80-Pin LQFP

Figure 3 shows the pinout of the 64-pin LQFP and QFP.



Figure 3. MCF51AC256 Series ColdFire Microcontroller 64-Pin QFP/LQFP

Figure 4 shows the pinout of the 44-pin LQFP.



Figure 4. MCF51AC256 Series ColdFire Microcontroller 44-Pin LQFP

Table 4 shows the package pin assignments.

Pir	n Num	ber	Lowest < Priority> Highest					
80	64	44	Port Pin	Alt 1	Alt 2	Alt 3		
1	1	1	PTC4	SS2				
2	2	2	IRQ	TPMCLK <sup>1</sup>				
3	3	3	RESET					
4	4	4	PTF0	RGPIO8	FTM1CH2			
5	5	5	PTF1	RGPIO9	FTM1CH3			
6	6	_	PTF2	RGPIO10	FTM1CH4			
7	7	_	PTF3	RGPI011	FTM1CH5			

Table 4. Pin Availability by Package Pin-Count

Pir	n Num	ber	Low	est < Prio	ority> Hi	ghest
80	64	44	Port Pin	Alt 1	Alt 2	Alt 3
8	8	6	PTF4	RGPIO12	FTM2CH0	
9	9	_	PTC6	FTM2FLT		
10	10	_	PTF7	RGPIO15		
11	11	7	PTF5	RGPIO13	FTM2CH1	
12	12	_	PTF6	RGPIO14	FTM1FLT	
13	_	_	PTJ0	PST0		
14	—	_	PTJ1	PST1		
15	_	_	PTJ2	PST2		
16	_	—	PTJ3	PST3		
17	13	8	PTE0	RGPIO0	TxD1	
18	14	9	PTE1	RGPIO1	RxD1	
19	15	10	PTE2	RGPIO2	FTM1CH0	
20	16	11	PTE3	RGPIO3	FTM1CH1	
21	17	12	PTE4	RGPIO4	SS1	
22	18	13	PTE5	RGPIO5	MISO1	
23	19	14	PTE6	RGPIO6	MOSI1	
24	20	15	PTE7	RGPI07	SPSCK1	
25	21	16	V <sub>SS</sub>			
26	22	17	$V_{DD}$			
27	_	_	PTJ4	DDATA0		
28	—	_	PTJ5	DDATA1		
29	_	_	PTJ6	DDATA2		
30	—	-	PTJ7	DDATA3		
31	23	18	PTG0	KBI1P0		
32	24	19	PTG1	KBI1P1		
33	25	20	PTG2	KBI1P2		
34	26	21	PTA0	TxCAN <sup>2</sup>		
35	27	22	PTA1	RxCAN <sup>3</sup>		
36	28	_	PTA2			
37	29	—	PTA3	ACMP2O		
38	30	—	PTA4	ACMP2-		
39	31	—	PTA5	ACMP2+		
40	32	—	PTA6	AD1P16		
41	33	—	PTA7	AD1P17		
42			PTH0	FTM2CH2	AD1P20	
43			PTH1	FTM2CH3	PSTCLK0	AD1P21
44			PTH2	FTM2CH4	PSTCLK1	AD1P22
45			PTH3	FTM2CH5	BKPT	AD1P23
46	34	23	PTB0	TPM3CH0	AD1P0	
47	35	24	PTB1	TPM3CH1	AD1P1	
48	36	25	PTB2	AD1P2		

Pir	n Num	ber	Low	est < Pric	ority> H	ighest
80	64	44	Port Pin	Alt 1	Alt 2	Alt 3
49	37	26	PTB3	AD1P3		
50	38	_	PTB4	AD1P4		
51	39	_	PTB5	AD1P5		
52	40	_	PTB6	AD1P6		
53	41	_	PTB7	AD1P7		
54	42	27	PTD0	AD1P8	ACMP1+	
55	43	28	PTD1	AD1P9	ACMP1-	
56	44	29	$V_{DDA}$			
57	45	30	V <sub>SSA</sub>			
58	46	31	PTD2	KBI1P5	AD1P10	ACMP10
59	47	32	PTD3	KBI1P6	AD1P11	
60	48	33	PTG3	KBI1P3	AD1P18	
61	49	—	PTG4	KBI1P4	AD1P19	
62	50	_	PTD4	FTM2CLK	AD1P12	
63	51	_	PTD5	AD1P13		
64	52	—	PTD6	FTM1CLK	AD1P14	
65	53	—	PTD7	KBI1P7	AD1P15	
66	54	34	V <sub>REFH</sub>			
67	55	35	V <sub>REFL</sub>			
68	56	36	BKGD	MS		
69	57	37	PTG5	XTAL		
70	58	38	PTG6	EXTAL		
71	59	39	V <sub>SS</sub>			
72	_	—	V <sub>DD</sub>			
73	60	40	PTC0	SCL1		
74	61	41	PTC1	SDA1		
75	_	—	PTH4	SPCK2		
76	—	—	PTH5	MOSI2		
77	_	—	PTH6	MISO2		
78	62	42	PTC2	MCLK		
79	63	43	PTC3	TxD2		
80	64	44	PTC5	RxD2		

Table 4. Pin Availability by Package Pin-Count (continued)

<sup>1</sup> TPMCLK, FTM1CLK, and FTM2CLK options are configured via software; out of reset, FTM1CLK, FTM2CLK, and TPMCLK are available to FTM1, FTM2, and TPM3 respectively.

 $^2$  TxCAN is available in the member that supports CAN.

<sup>3</sup> RxCAN is available in the member that supports CAN.

This section contains electrical specification tables and reference timing diagrams for the MCF51AC256 microcontroller, including detailed information on power considerations, DC/AC electrical characteristics, and AC timing specifications.

The electrical specifications are preliminary and are from previous designs or design simulations. These specifications may not be fully tested or guaranteed at this early stage of the product life cycle. These specifications will, however, be met for production silicon. Finalized specifications will be published after complete characterization and device qualifications have been completed.

## NOTE

The parameters specified in this data sheet supersede any values found in the module specifications.

## 2.1 Parameter Classification

The electrical parameters shown in this supplement are guaranteed by various methods. To give the customer a better understanding the following classification is used and the parameters are tagged accordingly in the tables where appropriate:

## Table 5. Parameter Classifications

Р	Those parameters are guaranteed during production testing on each individual device.
с	Those parameters are achieved by the design characterization by measuring a statistically relevant sample size across process variations.
т	Those parameters are achieved by design characterization on a small sample size from typical devices under typical conditions unless otherwise noted. All values shown in the typical column are within this category.
D	Those parameters are derived mainly from simulations.

## NOTE

The classification is shown in the column labeled "C" in the parameter tables where appropriate.

# 2.2 Absolute Maximum Ratings

Absolute maximum ratings are stress ratings only, and functional operation at the maxima is not guaranteed. Stress beyond the limits specified in Table 6 may affect device reliability or cause permanent damage to the device. For functional operating conditions, refer to the remaining tables in this section.

This device contains circuitry protecting against damage due to high static voltage or electrical fields; however, it is advised that normal precautions be taken to avoid application of any voltages higher than maximum-rated voltages to this high-impedance circuit. Reliability of operation is enhanced if unused inputs are tied to an appropriate logic voltage level (for instance, either  $V_{SS}$  or  $V_{DD}$ ).

Rating	Symbol	Value	Unit
Supply voltage	V <sub>DD</sub>	-0.3 to 5.8	V
Input voltage	V <sub>In</sub>	-0.3 to V <sub>DD</sub> + 0.3	V
Instantaneous maximum current Single pin limit (applies to all port pins) <sup>1</sup> , <sup>2</sup> , <sup>3</sup>	۱ <sub>D</sub>	±25	mA
Maximum current into V <sub>DD</sub>	I <sub>DD</sub>	120	mA
Storage temperature	T <sub>stg</sub>	-55 to 150	°C

## Table 6. Absolute Maximum Ratings

<sup>1</sup> Input must be current limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values for positive (V<sub>DD</sub>) and negative (V<sub>SS</sub>) clamp voltages, then use the larger of the two resistance values.

 $^2~$  All functional non-supply pins are internally clamped to  $V_{SS}$  and  $V_{DD}.$ 

<sup>3</sup> Power supply must maintain regulation within operating V<sub>DD</sub> range during instantaneous and operating maximum current conditions. If positive injection current (V<sub>In</sub> > V<sub>DD</sub>) is greater than I<sub>DD</sub>, the injection current may flow out of V<sub>DD</sub> and could result in external power supply going out of regulation. Ensure external V<sub>DD</sub> load will shunt current greater than maximum injection current. This will be the greatest risk when the MCU is not consuming power. Examples are: if no system clock is present, or if the clock rate is very low which would reduce overall power consumption.

## 2.3 Thermal Characteristics

This section provides information about operating temperature range, power dissipation, and package thermal resistance. Power dissipation on I/O pins is usually small compared to the power dissipation in on-chip logic and it is user-determined rather than being controlled by the MCU design. In order to take  $P_{I/O}$  into account in power calculations, determine the difference between actual pin voltage and  $V_{SS}$  or  $V_{DD}$  and multiply by the pin current for each I/O pin. Except in cases of unusually high pin current (heavy loads), the difference between pin voltage and  $V_{SS}$  or  $V_{DD}$  will be very small.

Rating		Symbol	Value	Unit
Operating temperature range (packaged)		T <sub>A</sub>	-40 to 105	°C
Maximum junction temperature		TJ	150	°C
Thermal resistance 1,2,3,4				
80-pin LQFP 64-pin LQFP	1s 2s2p 1s 2s2p	θυΑ	51 38 59 41	°C/W
64-pin QFP	2029	°JA		0/11
44-pin LQFP	1s 2s2p		50 36	
· · p –	1s 2s2p		67 45	

- <sup>1</sup> Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance
- <sup>2</sup> Junction to Ambient Natural Convection
- <sup>3</sup> 1s Single layer board, one signal layer
- <sup>4</sup> 2s2p Four layer board, 2 signal and 2 power layers

The average chip-junction temperature  $(T_J)$  in °C can be obtained from:

$$T_{J} = T_{A} + (P_{D} \times \theta_{JA})$$
 Eqn. 1

where:

 $T_A =$  Ambient temperature, °C

 $\theta_{JA}$  = Package thermal resistance, junction-to-ambient, °C/W

 $P_D = P_{int} + P_{I/O}$ 

 $P_{int} = I_{DD} \times V_{DD}$ , Watts — chip internal power

 $P_{I/O}$  = Power dissipation on input and output pins — user determined

For most applications,  $P_{I/O} \ll P_{int}$  and can be neglected. An approximate relationship between  $P_D$  and  $T_J$  (if  $P_{I/O}$  is neglected) is:

$$P_{D} = K \div (T_{J} + 273^{\circ}C)$$
 Eqn. 2

Solving Equation 1 and Equation 2 for K gives:

$$K = P_D \times (T_A + 273^{\circ}C) + \theta_{JA} \times (P_D)^2 \qquad \qquad Eqn. 3$$

where K is a constant pertaining to the particular part. K can be determined from Equation 3 by measuring  $P_D$  (at equilibrium) for a known  $T_A$ . Using this value of K, the values of  $P_D$  and  $T_J$  can be obtained by solving Equation 1 and Equation 2 iteratively for any value of  $T_A$ .

## 2.4 Electrostatic Discharge (ESD) Protection Characteristics

Although damage from static discharge is much less common on these devices than on early CMOS circuits, normal handling precautions should be used to avoid exposure to static discharge. Qualification tests are performed to ensure that these devices can withstand exposure to reasonable levels of static without suffering any permanent damage.

All ESD testing is in conformity with CDF-AEC-Q00 Stress Test Qualification for Automotive Grade Integrated Circuits. (http://www.aecouncil.com/) This device was qualified to AEC-Q100 Rev E.

A device is considered to have failed if, after exposure to ESD pulses, the device no longer meets the device specification requirements. Complete dc parametric and functional testing is performed per the

applicable device specification at room temperature followed by hot temperature, unless specified otherwise in the device specification.

Model	Description	Symbol	Value	Unit
Human body	Series resistance	R1	1500	Ω
	Storage capacitance	InceR11500 $\Omega$ citanceC100pFse per pin3inceR10 $\Omega$ citanceC0pFse per pin3citanceC0pFse per pin3t voltage limit2.5V	pF	
	Number of pulse per pin			
Charge device	Series resistance	R1	0	Ω
model	Storage capacitance	С	0	pF
	Number of pulse per pin	R1     1500       C     100       —     3       R1     0       C     0       —     3       —     -2.5	_	
Latch-up	Minimum input voltage limit	—	-2.5	V
	Maximum input voltage limit	—	7.5	V

Table 8. ESD and Latch-up Test Conditions

## Table 9. ESD and Latch-Up Protection Characteristics

Num	Rating	Symbol	Min	Max	Unit
1	Human body model (HBM)	V <sub>HBM</sub>	±2000	_	V
2	Charge device model (CDM)	V <sub>CDM</sub>	±500	—	V
3	Latch-up current at $T_A = 85 \ ^{\circ}C$	I <sub>LAT</sub>	±100		mA

# 2.5 DC Characteristics

This section includes information about power supply requirements, I/O pin characteristics, and power supply current in various operating modes.

Num	С	Parameter	Symbol	Min	Typical <sup>1</sup>	Max	Unit
1	-	Operating voltage		2.7		5.5	V
2	Р	Output high voltage — Low drive (PTxDSn = 0) $5 V$ , $I_{Load} = -4 mA$ $3 V$ , $I_{Load} = -2 mA$ $5 V$ , $I_{Load} = -2 mA$ $3 V$ , $I_{Load} = -1 mA$ Output high voltage — High drive (PTxDSn = 1) $5 V$ , $I_{Load} = -15 mA$ $3 V$ , $I_{Load} = -8 mA$ $5 V$ , $I_{Load} = -8 mA$ $3 V$ , $I_{Load} = -8 mA$ $3 V$ , $I_{Load} = -4 mA$	V <sub>OH</sub>	$V_{DD} - 1.5$ $V_{DD} - 1.5$ $V_{DD} - 0.8$ $V_{DD} - 0.8$ $V_{DD} - 1.5$ $V_{DD} - 1.5$ $V_{DD} - 0.8$ $V_{DD} - 0.8$			V

Table 10. DC Characteristics

Num	С	Parameter	Symbol	Min	Typical <sup>1</sup>	Мах	Unit
3	Р	Output low voltage — Low Drive (PTxDSn = 0) $5 \text{ V}, \text{ I}_{\text{Load}} = 4 \text{ m}$ $3 \text{ V}, \text{ I}_{\text{Load}} = 2 \text{ m}$ $5 \text{ V}, \text{ I}_{\text{Load}} = 2 \text{ m}$ $3 \text{ V}, \text{ I}_{\text{Load}} = 1 \text{ m}$	A	_	_	Max         1.5         1.5         0.8         1.5         0.8         1.5         0.8         1.00         60         100         60         0.35 × V_DD            1         65         65         8         2.0            4.5         4.6         2.7         2.72         4.5         4.6         2.7         2.72         4.5         4.6         2.7         2.72	V
	•	Output low voltage — High Drive (PTxDSn = 1) $5 \text{ V}, \text{ I}_{\text{Load}} = 15 \text{ m}$ $3 \text{ V}, \text{ I}_{\text{Load}} = 8 \text{ m}$ $5 \text{ V}, \text{ I}_{\text{Load}} = 8 \text{ m}$ $3 \text{ V}, \text{ I}_{\text{Load}} = 4 \text{ m}$	A A A	_	_	1.5 0.8	·
4	С		V I <sub>OHT</sub> V	_	_		mA
5	С	Output low current — Max total I <sub>OL</sub> for all ports 5 3		_	_		mA
6	Ρ	Input high voltage; all digital inputs	V <sub>IH</sub>	$0.65 \times V_{DD}$	_	—	V
7	Р	Input low voltage; all digital inputs	V <sub>IL</sub>	—	—	$0.35 \times V_{DD}$	V
8	D	Input hysteresis; all digital inputs	V <sub>hys</sub>	$0.06 \times V_{DD}$	—	—	mV
9	Ρ	Input leakage current; input only pins <sup>2</sup>	<sub>In</sub>	—	0.1	1	μA
10	Р	High impedance (off-state) leakage current <sup>2</sup>	ll <sub>oz</sub> l	—	0.1	1	μA
11	Р	Internal pullup resistors <sup>3</sup>	R <sub>PU</sub>	20	45	65	kΩ
12	Р	Internal pulldown resistors <sup>4</sup>	R <sub>PD</sub>	20	45	65	kΩ
13	С	Input capacitance; all non-supply pins	C <sub>In</sub>	—	—	8	pF
14	Ρ	POR rearm voltage	V <sub>POR</sub>	0.9	1.4	2.0	V
15	D	POR rearm time	t <sub>POR</sub>	10	—	—	μs
16	Ρ	Low-voltage detection threshold — high range V <sub>DD</sub> fallir V <sub>DD</sub> risir		4.2 4.27	4.35 4.4		V
17	Ρ	Low-voltage detection threshold — low range V <sub>DD</sub> fallir V <sub>DD</sub> risir	g V <sub>LVDL</sub>	2.48 2.5	2.68 2.7		V
18	Ρ	Low-voltage warning threshold — high range V <sub>DD</sub> fallir V <sub>DD</sub> risir		4.2 4.27	4.4 4.45		V
19	Ρ	Low-voltage warning threshold low range V <sub>DD</sub> fallir V <sub>DD</sub> risir		2.48 2.5	2.68 2.7		V
20	Т	Low-voltage inhibit reset/recover hysteresis 5 3		_	100 60	_	mV
21	D	RAM retention voltage	V <sub>RAM</sub>	—	0.6	1.0	V

## Table 10. DC Characteristics (continued)

Num	С	Parameter	Symbol	Min	Typical <sup>1</sup>	Max	Unit
		DC injection current <sup>5 6 7 8</sup> (single pin limit) $$V_{IN}\!>\!V_{DD}$ V_{IN}\!<\!V_{SS}$$		0 0	_	2 0.2	mA
22	D	DC injection current (Total MCU limit, includes sum of all stressed pins) V <sub>IN</sub> >V <sub>DD</sub> V <sub>IN</sub> <v<sub>SS</v<sub>	Ι <sub>ΙC</sub>	0 0	_	25 -5	mA

Table 10. DC Characteristics (continued)

<sup>1</sup> Typical values are based on characterization data at 25°C unless otherwise stated.

<sup>2</sup> Measured with  $V_{In} = V_{DD}$  or  $V_{SS}$ .

<sup>3</sup> Measured with  $V_{In} = V_{SS}$ .

<sup>4</sup> Measured with  $V_{In} = V_{DD}$ .

<sup>5</sup> Power supply must maintain regulation within operating  $V_{DD}$  range during instantaneous and operating maximum current conditions. If positive injection current ( $V_{In} > V_{DD}$ ) is greater than  $I_{DD}$ , the injection current may flow out of  $V_{DD}$  and could result in external power supply going out of regulation. Ensure external  $V_{DD}$  load will shunt current greater than maximum injection current. This will be the greatest risk when the MCU is not consuming power. Examples are: if no system clock is present, or if clock rate is very low (which would reduce overall power consumption).

 $^{6}$  All functional non-supply pins are internally clamped to V<sub>SS</sub> and V<sub>DD</sub>.

<sup>7</sup> Input must be current limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values for positive and negative clamp voltages, then use the larger of the two values.

<sup>8</sup> The RESET pin does not have a clamp diode to  $V_{DD}$ . Do not drive this pin above  $V_{DD}$ .



Figure 5. Typical I<sub>OH</sub> vs. V<sub>DD</sub>-V<sub>OH</sub> at V<sub>DD</sub> = 3 V (Low Drive, PTxDSn = 0)



Figure 6. Typical  $I_{OH}$  vs.  $V_{DD}$ - $V_{OH}$  at  $V_{DD}$  = 3 V (High Drive, PTxDSn = 1)



Figure 7. Typical  $I_{OH}$  vs.  $V_{DD}$ - $V_{OH}$  at  $V_{DD}$  = 5 V (Low Drive, PTxDSn = 0)



Figure 8. Typical I<sub>OH</sub> vs.  $V_{DD}$ – $V_{OH}$  at  $V_{DD}$  = 5 V (High Drive, PTxDSn = 1)

# 2.6 Supply Current Characteristics

Table 11. Supply Current Characteristics

Num	С	Parameter	Symbol	V <sub>DD</sub> (V)	Typical <sup>1</sup>	Max <sup>2</sup>	Unit	
			0 M⊔-		5	2.27	—	
			2 MHz		3.3	2.24	—	
			4 MHz		5	3.67	—	-
1	т	Run supply current measured at			3.3	3.64	_	
•	1	FEI mode, all modules off, system clock at:	8 MHz		5	6.55	—	
					3.3	6.54	—	
			16 MHz		5	11.90	—	
					3.3	11.85	_	
			2 MHz	-	5	3.28	_	]
			2 1011 12		3.3	3.26	_	
			4 MHz		5	4.33		]
2 T	т	Run supply current measured at	4 1011 12		3.3	4.32	—	
		FEI mode, all modules on, system clock at:	8 MHz		5	8.17	—	
					3.3	8.05	_	
			16 MHz RI <sub>DD</sub>	5	14.8	—	7	
				RI <sub>DD</sub>	3.3	14.74	—	mA
		2 MHz Bun supply current measured at 4 MHz	2 MHz		5	3.28	—	
					3.3	3.26	—	
				5	4.69	—		
3	т	Run supply current measured at FBE mode, all modules off			3.3	4.67	—	
		(RANGE = 1, HGO = 0), system	8 MHz		5	7.48	—	
		clock at:	0 IVII IZ		3.3	7.46	—	
			16 MHz		5	13.10	—	
					3.3	13.07	—	7
			2 MHz		5	3.64	—	
					3.3	3.63	—	
		Pup oupply ourrent modeured at	4 MHz		5	5.38	—	-
4	т	Run supply current measured at FBE mode, all modules on			3.3	5.35	—	
		(RANGE = 1, HGO = 0), system	8 MHz		5	8.65		
		clock at:			3.3	8.64		
			16 MHz		5	15.55	_	
					3.3	15.40	_	

Num	С	Parameter	Symbol	V <sub>DD</sub> (V)	Typical <sup>1</sup>	Max <sup>2</sup>	Unit
F	с	Wait mode supply <sup>3</sup> current measured at		5	1.3	2	
5	C	(CPU clock = 2 MHz, f <sub>Bus</sub> = 1 MHz)		3	1.29	2	- mA
6	с	Wait mode supply <sup>3</sup> current measured at	WIRE	5	5.11	8	mA
0	Ŭ	(CPU clock = 16 MHz, f <sub>Bus</sub> = 8 MHz)	00	3	5.1	8	
7	с	Wait mode supply <sup>3</sup> current measured at		5	15.24	25	mA
•	Ŭ	(CPU clock = 50 MHz, f <sub>Bus</sub> = 25 MHz)	S2I <sub>DD</sub>	3	15.2	25	
8	с	Stop2 mode supply current -40 °C 25 °C 120 °C	C C S2I <sub>DD</sub>	5	1.40	2.5 2.5 200	μA
0	C	-40 °C 25 °C 120 °C	321 <sub>DD</sub>	3	1.16	2.5 2.5 200	μA
9	С	Stop3 mode supply current -40 °C 25 °C 120 °C	631	5	1.60	2.5 2.5 220	μA
9		-40 °C 25 °C 120 °C	331 <sub>DD</sub>	3	1.35	2.5 2.5 220	μA
10	с	RTI adder to stop2 or stop3 <sup>3</sup> , 25 °C	6031	5	300		nA
10			523 DDRTI	3	300		nA
11	С	Adder to stop3 for oscillator enabled <sup>4</sup> (ERCLKEN =1 and EREFSTEN = 1)	S3I <sub>DDOSC</sub>	5, 3	5		μA

<sup>1</sup> Typicals are measured at 25 °C.

<sup>2</sup> Values given here are preliminary estimates prior to completing characterization.

<sup>3</sup> Most customers are expected to find that auto-wakeup from stop2 or stop3 can be used instead of the higher current wait mode.

<sup>4</sup> Values given under the following conditions: low range operation (RANGE = 0), low power mode (HGO = 0).



Figure 9. Typical Run  $\mathrm{I}_{\mathrm{DD}}$  vs. System Clock Freq. for FEI and FBE Modes

# 2.7 Analog Comparator (ACMP) Electricals

## **Table 12. Analog Comparator Electrical Specifications**

Num	С	Rating	Symbol	Min	Typical	Max	Unit
1		Supply voltage	V <sub>DD</sub>	2.7		5.5	V
2	Т	Supply current (active)	I <sub>DDAC</sub>	—	20	35	μA
3	D	Analog input voltage	V <sub>AIN</sub>	V <sub>SS</sub> – 0.3	_	V <sub>DD</sub>	V
4	D	Analog input offset voltage	V <sub>AIO</sub>	—	20	40	mV
5	D	Analog comparator hysteresis	V <sub>H</sub>	3.0	6.0	20.0	mV
6	D	Analog input leakage current	I <sub>ALKG</sub>	—	_	1.0	μA
7	D	Analog comparator initialization delay	t <sub>AINIT</sub>	—	_	1.0	μS
8	Ρ	Bandgap voltage reference factory trimmed at $V_{DD}$ = 5.3248 V, Temp = 25 °C	V <sub>BG</sub>	1.18	1.20	1.21	V

# 2.8 ADC Characteristics

	•	<b>0</b>	0						•
Num	С	Characteristic	Conditions	Symb	Min	Typical <sup>1</sup>	Max	Unit	Comment
	D		Absolute	V <sub>DDA</sub>	2.7	—	5.5	V	
1	D	Supply voltage	Delta to V <sub>DD</sub> (V <sub>DD</sub> – V <sub>DDA</sub> ) <sup>2</sup>	$\Delta V_{DDA}$	-100	0	100	mV	
2	D	Ground voltage	Delta to V <sub>SS</sub> (V <sub>SS</sub> – V <sub>SSA</sub> ) <sup>2</sup>	$\Delta V_{SSA}$	-100	0	100	mV	
3	D	Reference voltage high		V <sub>REFH</sub>	2.7	V <sub>DDA</sub>	V <sub>DDA</sub>	v	
4	D	Reference voltage low		V <sub>REFL</sub>	V <sub>SSA</sub>	V <sub>SSA</sub>	V <sub>SSA</sub>	v	
5	D	Input voltage		V <sub>ADIN</sub>	V <sub>REFL</sub>	—	V <sub>REFH</sub>	V	
6	С	Input capacitance		C <sub>ADIN</sub>	_	4.5	5.5	pF	
7	С	Input resistance		R <sub>ADIN</sub>	_	3	5	kΩ	
	С		12-bit mode f <sub>ADCK</sub> > 4MHz f <sub>ADCK</sub> < 4MHz		_		2 5		
8	С	Analog source resistance	10-bit mode f <sub>ADCK</sub> > 4MHz f <sub>ADCK</sub> < 4MHz	R <sub>AS</sub>	_		5 10	kΩ	External to MCU
	С		8-bit mode (all valid f <sub>ADCK</sub> )		_	_	10		
9	D	ADC conversion	High speed (ADLPC = 0)	f	0.4	_	8.0	MHz	
3	D	clock frequency	Low power (ADLPC = 1)	- f <sub>ADCK</sub>	0.4		4.0		

<sup>1</sup> Typical values assume V<sub>DDA</sub> = 5.0 V, Temp = 25 °C, f<sub>ADCK</sub> = 1.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.

<sup>2</sup> DC potential difference.



Figure 10. ADC Input Impedance Equivalency Diagram

Num	С	Characteristic	Conditions	Symb	Min	Typical <sup>1</sup>	Мах	Unit	Comment			
1	т	Supply current ADLPC = 1 ADLSMP = 1 ADCO = 1		I <sub>DDA</sub>	_	133	_	μA				
2	т	Supply current ADLPC = 1 ADLSM = 0 ADCO = 1		I <sub>DDA</sub>	_	218	_	μA				
3	т	Supply current ADLPC = 0 ADLSMP = 1 ADCO = 1		I <sub>DDA</sub>	_	327	_	μA				
4	D	Supply current ADLPC = 0 ADLSMP = 0 ADCO = 1		I <sub>DDA</sub>	_	0.582	1	mA				
5	Т	Supply current	Stop, reset, module off	I <sub>DDA</sub>		0.011	1	μA				
0	P	ADC High speed (ADLPC = 0)		2	3.3	5	N 41 1-	t <sub>ADACK</sub> =				
6	Р	asynchronous clock source	Low power (ADLPC = 1)	f <sub>ADACK</sub>	f <sub>ADACK</sub>	f <sub>ADACK</sub>	f <sub>ADACK</sub>	1.25	2	3.3	MHz	<sup>t</sup> ADACK – 1/f <sub>ADACK</sub>

Table 14. 5 Volt 12-bit ADC Characteristics ( $V_{REFH} = V_{DDA}$ ,  $V_{REFL} = V_{SSA}$ )

	1	1	1	(VREFH = VDDA, VREFL = VSSA) (Communded)					
Num	С	Characteristic	Conditions	Symb	Min	Typical <sup>1</sup>	Max	Unit	Comment
7		Conversion	Short sample (ADLSMP = 0)		—	20	_	ADCK	See
7	Р	time (including sample time)	Long sample (ADLSMP = 1)	t <sub>ADC</sub>	—	40		cycles	Table 10 for
0	-	Completing	Short sample (ADLSMP = 0)		—	3.5		ADCK	conversion time
8	Т	Sample time	Long sample (ADLSMP = 1)	t <sub>ADS</sub>	_	23.5		cycles	variances
	Т	Total	12-bit mode		_	±3.0			Includes
9	Р	unadjusted	10-bit mode	E <sub>TUE</sub> —	±1	±2.5	LSB <sup>2</sup>	quantizatio	
	Т	error	8-bit mode		_	±0.5	±1.0		n
	Т		12-bit mode		_	±1.75			
10	Р	Differential non-linearity	10-bit mode <sup>3</sup>	DNL	_	±0.5	±1.0	LSB <sup>2</sup>	
	Т		8-bit mode <sup>3</sup>		_	±0.3	±0.5		
	Т		12-bit mode		—	±1.5			
11	Т	Integral non-linearity	10-bit mode	INL	_	±0.5	±1.0	LSB <sup>2</sup>	
	Т		8-bit mode		_	±0.3	±0.5		
	Т		12-bit mode		—	±1.5			
12	Р	Zero-scale error	10-bit mode	E <sub>ZS</sub>	_	±0.5	±1.5	LSB <sup>2</sup>	V <sub>ADIN</sub> = V <sub>SSA</sub>
	Т		8-bit mode		_	±0.5	±0.5		- 354
	Т		12-bit mode		_	±1			
13	Р	Full-scale error	10-bit mode	E <sub>FS</sub>	_	±0.5	±1	LSB <sup>2</sup>	V <sub>ADIN</sub> = V <sub>DDA</sub>
	Т		8-bit mode		_	±0.5	±0.5		DDA
			12-bit mode		_	-1 to 0			
14	D	Quantization error	10-bit mode	EQ	_	_	±0.5	LSB <sup>2</sup>	
			8-bit mode		_	_	±0.5		
			12-bit mode		_	±1	_		Pad
15	D	Input leakage error	10-bit mode	E <sub>IL</sub>	_	±0.2	±2.5	LSB <sup>2</sup>	leakage <sup>4</sup> *
			8-bit mode		_	±0.1	±1		R <sub>AS</sub>
16	D	Temp sensor voltage	25°C	V <sub>TEMP25</sub>	_	1.396	_	V	
17		Temp sensor	–40 °C–25 °C	~	—	3.266		mV/°C	
17	D	slope	25 °C–85 °C	m	_	3.638	_	mv/°C	
	1	1							1

## Table 14. 5 Volt 12-bit ADC Characteristics ( $V_{REFH} = V_{DDA}$ , $V_{REFL} = V_{SSA}$ ) (continued)

<sup>1</sup> Typical values assume V<sub>DDA</sub> = 5.0 V, Temp = 25 °C, f<sub>ADCK</sub> = 1.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.

<sup>2</sup> 1 LSB =  $(V_{\text{REFH}} - V_{\text{REFL}})/2^{N}$ .

- <sup>3</sup> Monotonicity and No-Missing-Codes guaranteed in 10-bit and 8-bit modes
- <sup>4</sup> Based on input pad leakage current. Refer to pad electricals.

# 2.9 External Oscillator (XOSC) Characteristics

## Table 15. Oscillator Electrical Specifications (Temperature Range = -40 to 105 °C Ambient)

Num	С	Rating	Symbol	Min	Typical <sup>1</sup>	Мах	Unit
1	С	Oscillator crystal or resonator (EREFS = 1, ERCLKEN = 1) Low range (RANGE = 0) High range (RANGE = 1) FEE or FBE mode <sup>2</sup> High range (RANGE = 1) PEE or PBE mode <sup>3</sup> High range (RANGE = 1, HGO = 1) BLPE mode High range (RANGE = 1, HGO = 0) BLPE mode	f <sub>lo</sub> f <sub>hi-fll</sub> f <sub>hi-pll</sub> f <sub>hi-hgo</sub> f <sub>hi-lp</sub>	32 1 1 1 1	     	38.4 5 16 16 8	kHz MHz MHz MHz MHz MHz
2		Load capacitors	C <sub>1</sub> C <sub>2</sub>		e crystal o acturer's ree		
3	_	Feedback resistor Low range (32 kHz to 38.4 kHz) High range (1 MHz to 16 MHz)	R <sub>F</sub>		10 1		MΩ
4		Series resistor Low range, low gain (RANGE = 0, HGO = 0) Low range, high gain (RANGE = 0, HGO = 1) High range, low gain (RANGE = 1, HGO = 0) High range, high gain (RANGE = 1, HGO = 1) ≥ 8 MHz 4 MHz 1 MHz	R <sub>S</sub>		0 100 0 0 0 0	  10 20	kΩ
5	Т	Crystal start-up time <sup>4</sup> Low range, low gain (RANGE = 0, HGO = 0) Low range, high gain (RANGE = 0, HGO = 1) High range, low gain (RANGE = 1, HGO = 0) <sup>5</sup> High range, high gain (RANGE = 1, HGO = 1) <sup>5</sup>	t CSTL-LP CSTL-HGO CSTH-LP t CSTH-HGO		200 400 5 15		ms
6	т	Square wave input clock frequency (EREFS = 0, ERCLKEN = 1) FEE or FBE mode <sup>2</sup> PEE or PBE mode <sup>3</sup> BLPE mode	f <sub>extal</sub>	0.03125 1 0	—	5 16 40	MHz

<sup>1</sup> Data in Typical column was characterized at 5.0 V, 25 °C or is typical recommended value.

<sup>2</sup> When MCG is configured for FEE or FBE mode, input clock source must be divisible using RDIV to within the range of 31.25 kHz to 39.0625 kHz.

<sup>3</sup> When MCG is configured for PEE or PBE mode, input clock source must be divisible using RDIV to within the range of 1 MHz to 2 MHz.

<sup>4</sup> This parameter is characterized and not tested on each device. Proper PC board layout procedures must be followed to achieve specifications.

<sup>5</sup> 4 MHz crystal



# 2.10 MCG Specifications

## Table 16. MCG Frequency Specifications (Temperature Range = -40 to 105 °C Ambient)

Num	С	Rat	ing	Symbol	Min	Typical <sup>1</sup>	Max	Unit
1	С	Internal reference frequence $V_{DD} = 5 V$ and temperature	y — factory trimmed at = 25 °C	f <sub>int_ft</sub>	_	32.768	_	kHz
2	С	DCO output frequency range — untrimmed <sup>2</sup> Mid range (DRS=         High range (DRS=         DCO output frequency <sup>2</sup> reference =32768Hz and DMX32 = 1       Low range (DRS=         Resolution of trimmed DCO output frequency at voltage and temperature (using FTRIM)       High range (DRS=         Resolution of trimmed DCO output frequency at voltage and temperature (not using FTRIM)       Total deviation of trimmed DCO output frequency at voltage and temperature (not using FTRIM)         Total deviation of trimmed DCO output frequency fixed voltage and temperature       Total deviation of trimmed DCO output frequency output frequency fixed voltage and temperature         Total deviation of trimmed DCO output frequency fixed voltage and temperature       DCO output frequency fixed voltage and temperature         Total deviation of trimmed DCO output frequency fixed voltage and temperature       DCO output frequency fixed voltage and temperature         Total deviation of trimmed DCO output frequency fixed voltage and temperature       DCO output frequency fixed voltage and temperature         FLL acquisition time <sup>3</sup> PLL acquisition time <sup>4</sup> Long term jitter of DCO output clock (averaged 2ms interval) <sup>5</sup>		f <sub>int_ut</sub>	31.25	—	39.0625	kHz
3	Т	Internal reference startup ti	me	t <sub>irefst</sub>	_	60	100	μs
	С		Low range (DRS=00)		16	—	20	
4	С	DCO output frequency	Mid range (DRS=01)	f <sub>dco_ut</sub>	32	—	40	MHz
	С	ango antininoa	High range (DRS=10)		48	—	60	
	Ρ	DCO output frequency <sup>2</sup>	Low range (DRS=00)	f <sub>dco_DMX32</sub>		16.82		
5	Ρ	reference =32768Hz	Mid range (DRS=01)			33.69		MHz
	Ρ	and DMX32 = 1	High range (DRS=10)			50.48	_	
6	D	Resolution of trimmed DCO output frequency at fixed voltage and temperature (using FTRIM)		$\Delta f_{dco\_res\_t}$	_	±0.1	±0.2	%f <sub>dco</sub>
7	D			$\Delta f_{dco\_res\_t}$	_	±0.2	±0.4	%f <sub>dco</sub>
8	D		CO output frequency over	$\Delta f_{dco_t}$	_	0.5 -1.0	±2	%f <sub>dco</sub>
9	D			$\Delta f_{dco_t}$	_	±0.5	±1	%f <sub>dco</sub>
10	D	FLL acquisition time <sup>3</sup>		t <sub>fll_acquire</sub>		—	1	ms
11	D	PLL acquisition time <sup>4</sup>		t <sub>pll_acquire</sub>		—	1	ms
12	D		put clock (averaged over	C <sub>Jitter</sub>	_	0.02	0.2	%f <sub>dco</sub>
13	D	VCO operating frequency		f <sub>vco</sub>	7.0		55.0	MHz
16	D	Jitter of PLL output clock m	easured over 625 ns <sup>6</sup>	f <sub>pll_jitter_625ns</sub>	_	0.566 <sup>6</sup>		%f <sub>pll</sub>
17	D	Lock entry frequency tolera	ince <sup>7</sup>	D <sub>lock</sub>	±1.49	—	±2.98	%

Num	С	Rating	Symbol	Min	Typical <sup>1</sup>	Max	Unit
18	D	Lock exit frequency tolerance <sup>8</sup>	D <sub>unl</sub>	±4.47		±5.97	%
19	D	Lock time — FLL	t <sub>fll_lock</sub>	_	_	t <sub>fII_acquire+</sub> 1075(1/ <sup>f</sup> int_t)	S
20	D	Lock time — PLL	t <sub>pll_lock</sub>	_	_	t <sub>pll_acquire+</sub> 1075(1/ <sup>f</sup> pll_ref)	s
21	D	Loss of external clock minimum frequency — RANGE = 0	f <sub>loc_low</sub>	$(3/5) \times f_{int}$	_	_	kHz

<sup>1</sup> Data in Typical column was characterized at 5.0 V, 25 °C or is typical recommended value.

<sup>2</sup> The resulting bus clock frequency must not exceed the maximum specified bus clock frequency of the device.

<sup>3</sup> This specification applies when the FLL reference source or reference divider is changed, trim value changed or changing from FLL disabled (BLPE, BLPI) to FLL enabled (FEI, FEE, FBE, FBI). If a crystal/resonator is being used as the reference, this specification assumes it is already running.

<sup>4</sup> This specification applies when the PLL VCO divider or reference divider is changed, or changing from PLL disabled (BLPE, BLPI) to PLL enabled (PBE, PEE). If a crystal/resonator is being used as the reference, this specification assumes it is already running.

<sup>5</sup> Jitter is the average deviation from the programmed frequency measured over the specified interval at maximum f<sub>BUS</sub>. Measurements are made with the device powered by filtered supplies and clocked by a stable external clock signal. Noise injected into the FLL circuitry via V<sub>DD</sub> and V<sub>SS</sub> and variation in crystal oscillator frequency increase the C<sub>Jitter</sub> percentage for a given interval.

<sup>6</sup> 625 ns represents 5 time quanta for CAN applications, under worst case conditions of 8 MHz CAN bus clock, 1 Mbps CAN bus speed, and 8 time quanta per bit for bit time settings. 5 time quanta is the minimum time between a synchronization edge and the sample point of a bit using 8 time quanta per bit.

<sup>7</sup> Below D<sub>lock</sub> minimum, the MCG enters lock. Above D<sub>lock</sub> maximum, the MCG will not enter lock. But if the MCG is already in lock, then the MCG may stay in lock.

<sup>8</sup> Below D<sub>unl</sub> minimum, the MCG will not exit lock if already in lock. Above D<sub>unl</sub> maximum, the MCG is guaranteed to exit lock.

# 2.11 AC Characteristics

This section describes ac timing characteristics for each peripheral system.

## 2.11.1 Control Timing

Num	С	Parameter	Symbol	Min	Typical <sup>1</sup>	Max	Unit
1	D	Bus frequency (t <sub>cyc</sub> = 1/f <sub>Bus</sub> )	f <sub>Bus</sub>	dc	—	24	MHz
2	D	Internal low-power oscillator period	t <sub>LPO</sub>	800	—	1500	μs
3	D	External reset pulse width <sup>2</sup> (t <sub>cyc</sub> = 1/f <sub>Self_reset</sub> )	t <sub>extrst</sub>	100	_	_	ns
4	D	Reset low drive	t <sub>rstdrv</sub>	$66  imes t_{cyc}$	—		ns
5	D	Active background debug mode latch setup time	t <sub>MSSU</sub>	500	—		ns
6	D	Active background debug mode latch hold time	t <sub>MSH</sub>	100	—		ns
7	D	IRQ pulse width Asynchronous path <sup>2</sup> Synchronous path <sup>3</sup>	t <sub>ILIH,</sub> t <sub>IHIL</sub>	100 1.5 × t <sub>cyc</sub>	_	_	ns
8	D	KBIPx pulse width Asynchronous path <sup>2</sup> Synchronous path <sup>3</sup>	t <sub>ILIH,</sub> t <sub>IHIL</sub>	100 1.5 × t <sub>cyc</sub>	_	_	ns
9	D	Port rise and fall time $(load = 50 \text{ pF})^4$ Slew rate control disabled (PTxSE = 0), Low Drive Slew rate control enabled (PTxSE = 1), Low Drive Slew rate control disabled (PTxSE = 0), Low Drive Slew rate control enabled (PTxSE = 1), Low Drive	t <sub>Rise</sub> , t <sub>Fall</sub>	 	11 35 40 75	_	ns

Table 17. Control Timing

<sup>1</sup> Typical values are based on characterization data at  $V_{DD}$  = 5.0 V, 25 °C unless otherwise stated.

<sup>2</sup> This is the shortest pulse that is guaranteed to be recognized as a reset pin request. Shorter pulses are not guaranteed to override reset requests from internal sources.

<sup>3</sup> This is the minimum pulse width that is guaranteed to pass through the pin synchronization circuitry. Shorter pulses may or may not be recognized. In stop mode, the synchronizer is bypassed so shorter pulses can be recognized in that case.

 $^4$   $\,$  Timing is shown with respect to 20%  $V_{DD}$  and 80%  $V_{DD}$  levels. Temperature range –40 °C to 105 °C.



# 2.11.2 Timer (TPM/FTM) Module Timing

Synchronizer circuits determine the shortest input pulses that can be recognized or the fastest clock that can be used as the optional external source to the timer counter. These synchronizers operate from the current bus rate clock.

NUM	С	Function	Symbol	Min	Max	Unit
1	_	External clock frequency	f <sub>TPMext</sub>	DC	f <sub>Bus</sub> /4	MHz
2	—	External clock period	t <sub>TPMext</sub>	4	_	t <sub>cyc</sub>
3	D	External clock high time	t <sub>clkh</sub>	1.5	_	t <sub>cyc</sub>
4	D	External clock low time	t <sub>ciki</sub>	1.5	—	t <sub>cyc</sub>
5	D	Input capture pulse width	t <sub>ICPW</sub>	1.5		t <sub>cyc</sub>



Figure 13. Timer External Clock



Figure 14. Timer Input Capture Pulse

## 2.11.3 MSCAN

## Table 19. MSCAN Wake-Up Pulse Characteristics

Num	С	Parameter	Symbol	Min	Typical <sup>1</sup>	Мах	Unit
1	D	MSCAN wake-up dominant pulse filtered	t <sub>WUP</sub>	_		2	μs
2	D	MSCAN wake-up dominant pulse pass	t <sub>WUP</sub>	5	_	5	μs

<sup>1</sup> Typical values are based on characterization data at  $V_{DD}$  = 5.0 V, 25 °C unless otherwise stated.

# 2.12 SPI Characteristics

Table 20 and Figure 15 through Figure 18 describe the timing requirements for the SPI system.

No.	С	Function	Symbol	Min	Мах	Unit
_	D	Operating frequency Master Slave	f <sub>op</sub>	f <sub>Bus</sub> /2048 0	f <sub>Bus</sub> /2 f <sub>Bus</sub> /4	Hz
1	D	SPSCK period Master Slave	t <sub>SPSCK</sub>	2 4	2048 —	t <sub>cyc</sub> t <sub>cyc</sub>
2	D	Enable lead time Master Slave	t <sub>Lead</sub>	1/2 1		t <sub>SPSCK</sub> t <sub>cyc</sub>
3	D	Enable lag time Master Slave	t <sub>Lag</sub>	1/2 1		t <sub>SPSCK</sub> t <sub>cyc</sub>
4	D	Clock (SPSCK) high or low time Master Slave	twspsck	$t_{cyc} - 30$ $t_{cyc} - 30$	1024 t <sub>cyc</sub>	ns ns
5	D	Data setup time (inputs) Master Slave	t <sub>SU</sub>	15 15	_	ns ns
6	D	Data hold time (inputs) Master Slave	t <sub>HI</sub>	0 25		ns ns
7	D	Slave access time	t <sub>a</sub>	_	1	t <sub>cyc</sub>
8	D	Slave MISO disable time	t <sub>dis</sub>	_	1	t <sub>cyc</sub>
9	D	Data valid (after SPSCK edge) Master Slave	t <sub>v</sub>	_	25 25	ns ns
10	D	Data hold time (outputs) Master Slave	t <sub>HO</sub>	0 0		ns ns
11	D	Rise time Input Output	t <sub>RI</sub> t <sub>RO</sub>		t <sub>cyc</sub> – 25 25	ns ns
12	D	Fall time Input Output	t <sub>FI</sub> t <sub>FO</sub>		t <sub>cyc</sub> – 25 25	ns ns

## Table 20. SPI Timing



NOTES:

1. SS output mode (DDS7 = 1, SSOE = 1).

2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

#### Figure 15. SPI Master Timing (CPHA = 0)



NOTES:

1. SS output mode (DDS7 = 1, SSOE = 1).

2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

#### Figure 16. SPI Master Timing (CPHA =1)



1. Not defined but normally MSB of character just received





Figure 18. SPI Slave Timing (CPHA = 1)

## 2.13 Flash Specifications

This section provides details about program/erase times and program-erase endurance for the Flash memory.

Program and erase operations do not require any special power sources other than the normal  $V_{DD}$  supply. For more detailed information about program/erase operations, see Chapter 4, "Memory."

Num	С	Characteristic	Symbol	Min	Typical <sup>1</sup>	Max	Unit
1	—	Supply voltage for program/erase	V <sub>prog/erase</sub>	2.7	—	5.5	V
2	—	Supply voltage for read operation	V <sub>Read</sub>	2.7	—	5.5	V
3	—	Internal FCLK frequency <sup>2</sup>	f <sub>FCLK</sub>	150	—	200	kHz
4	—	Internal FCLK period (1/FCLK)	t <sub>Fcyc</sub>	5	—	6.67	μs
5	—	Byte program time (random location) <sup>2</sup>	t <sub>prog</sub>	9		t <sub>Fcyc</sub>	
6	—	Byte program time (burst mode) <sup>2</sup>	t <sub>Burst</sub>	4 t <sub>F</sub>		t <sub>Fcyc</sub>	
7	—	Page erase time <sup>3</sup>	t <sub>Page</sub>	4000 t <sub>Fc</sub>		t <sub>Fcyc</sub>	
8	—	Mass erase time <sup>2</sup>	t <sub>Mass</sub>	20,000		t <sub>Fcyc</sub>	
9	с	Program/erase endurance <sup>4</sup> $T_L$ to $T_H = -40 \text{ °C}$ to 105 °C T = 25  °C	_	10,000	 100,000	_	cycles
10	С	Data retention <sup>5</sup>	t <sub>D_ret</sub>	15	100	_	years

## Table 21. Flash Characteristics

<sup>1</sup> Typical values are based on characterization data at  $V_{DD}$  = 5.0 V, 25 °C unless otherwise stated.

<sup>2</sup> The frequency of this clock is controlled by a software setting.

<sup>3</sup> These values are hardware state machine controlled. User code does not need to count cycles. This information supplied for calculating approximate time to program and erase.

- <sup>4</sup> Typical endurance for flash was evaluated for this product family on the 9S12Dx64. For additional information on how Freescale Semiconductor defines typical endurance, please refer to Engineering Bulletin EB619/D, *Typical Endurance for Nonvolatile Memory.*
- <sup>5</sup> Typical data retention values are based on intrinsic capability of the technology measured at high temperature and de-rated to 25°C using the Arrhenius equation. For additional information on how Freescale Semiconductor defines typical data retention, please refer to Engineering Bulletin EB618/D, *Typical Data Retention for Nonvolatile Memory.*

# 2.14 EMC Performance

Electromagnetic compatibility (EMC) performance is highly dependant on the environment in which the MCU resides. Board design and layout, circuit topology choices, location and characteristics of external components as well as MCU software operation all play a significant role in EMC performance. The system designer should consult Freescale applications notes such as AN2321, AN1050, AN1263, AN2764, and AN1259 for advice and guidance specifically targeted at optimizing EMC performance.

## 2.14.1 Radiated Emissions

Microcontroller radiated RF emissions are measured from 150 kHz to 1 GHz using the TEM/GTEM Cell method in accordance with the IEC 61967-2 and SAE J1752/3 standards. The measurement is performed with the microcontroller installed on a custom EMC evaluation board while running specialized EMC test software. The radiated emissions from the microcontroller are measured in a TEM cell in two package orientations (North and East). For more detailed information concerning the evaluation results, conditions and setup, please refer to the EMC Evaluation Report for this device.

**Mechanical Outline Drawings** 

# 3 Mechanical Outline Drawings

Table 22 provides the available package types and their document numbers. The latest package outline/mechanical drawings are available on the MCF51AC256 Series Product Summary pages at http://www.freescale.com.

To view the latest drawing, either:

- Click on the appropriate link in Table 22, or
- Open a browser to the FreescaleÆ website (http://www.freescale.com), and enter the appropriate document number (from Table 22) in the "Enter Keyword" search box at the top of the page.

Pin Count	Туре	Document No.
80	LQFP	98ARL10530D
64	LQFP	98ASS23234W
64	QFP	98ASB42844B
44	LQFP	98ASS23225W

## Table 22. Package Information

# 4 Revision History

## Table 23. Revision History

Revision	Description	
1	Initial published	
2	Updated ADC channels, Item 1, 4-5 on Table 2.10	
3		
4	Corrected the expansion of SPI to serial peripheral interface.	
5	Updated V <sub>LVDL</sub> in the Table 10. Updated RI <sub>DD</sub> in the Table 11.	
6	Updated $V_{LVDH}$ , $V_{LVDL}$ , $V_{LVWH}$ and $V_{LVWL}$ in the Table 10. Added LPO on the Figure 1 and LPO features in the Section 1.3, "Features."	
7	Added 44-pin LQFP package information for AC256 and AC128.	

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